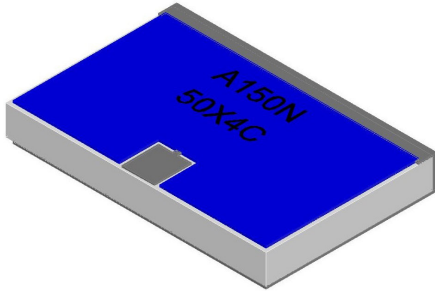


Chip Termination 150 Watts, 50Ω



Description

The A150N50X4C is high performance Aluminum Nitride (AlN) chip termination intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination dissipates 150W and has a return loss of 25dB to 3GHz. It is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators, and for use in power combiners. The termination is also RoHS compliant!

General Specifications

Features:

- RoHS Compliant
- 150 Watts
- DC – 3.0 GHz
- AlN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

Resistive Element	Thick film
Substrate	AlN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +150°C

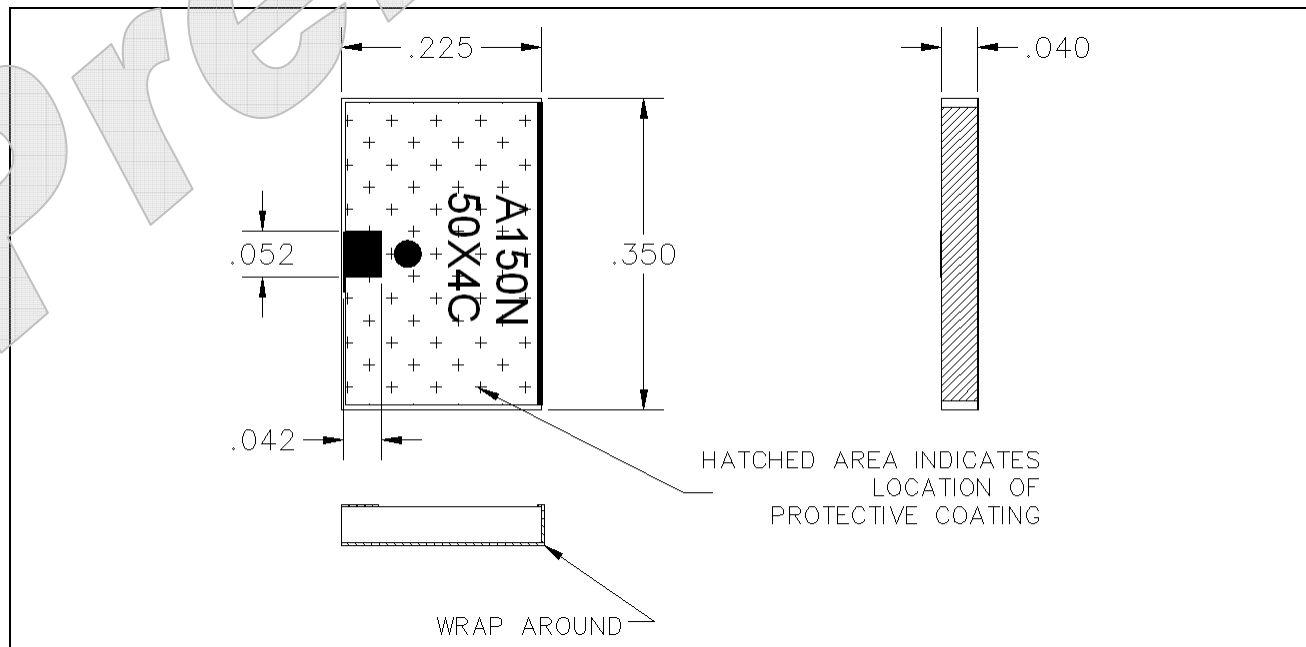
Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.

Electrical Specifications

Resistance Value:	50 Ohms, $\pm 2\%$
Power:	150 Watts
Frequency Range:	DC – 3.0 GHz
V.S.W.R.	1.12 : 1

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

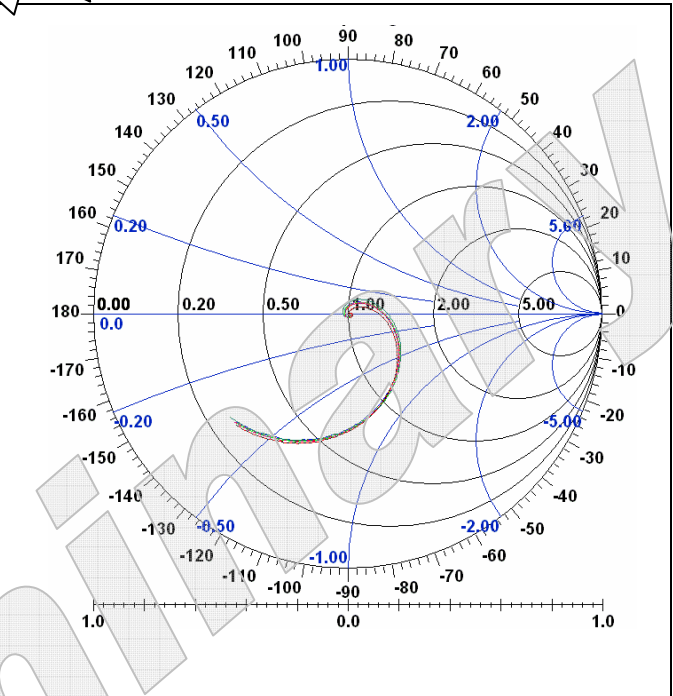
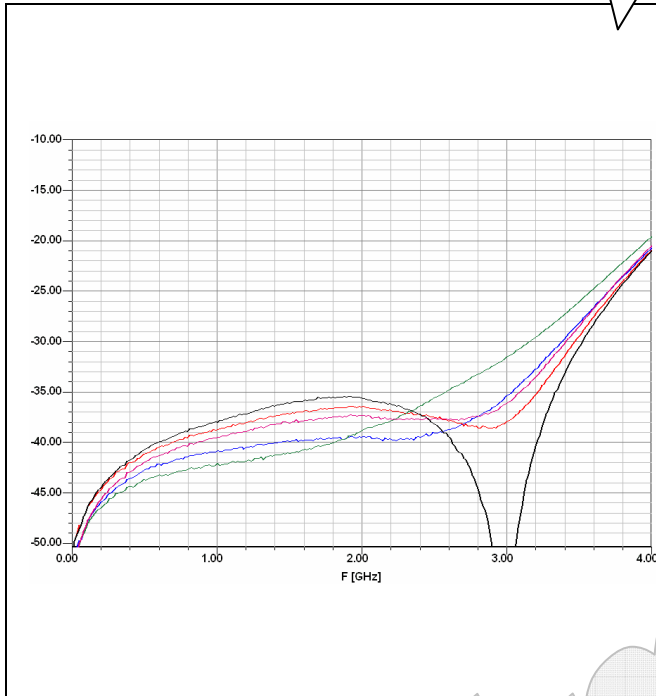
Outline Drawing



A150N50X4C (097) Rev D pg 1 of 2

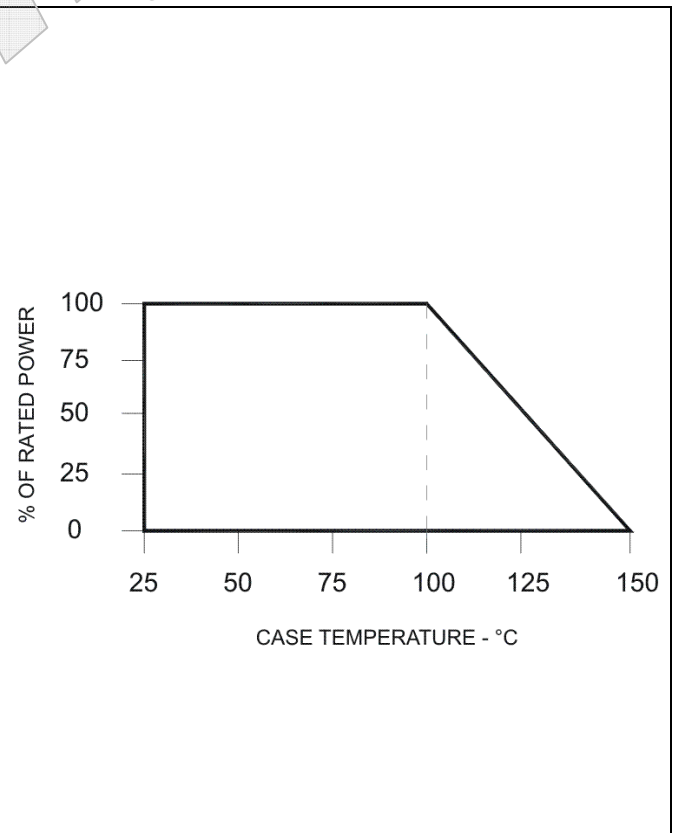
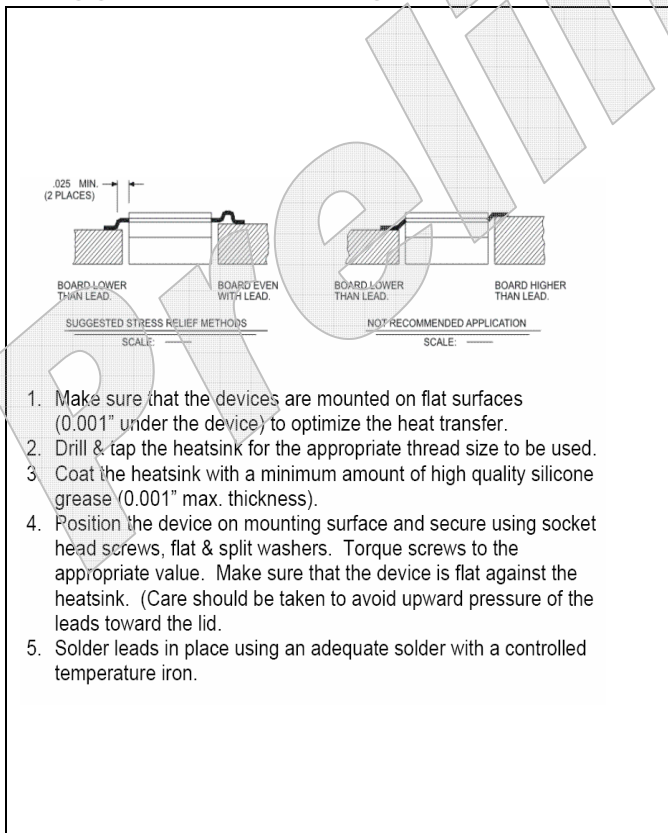
RoHS
Compliant

Typical Performance:



Suggested Mounting Procedures:

Derating:



A150N50X4C (097) Rev D pg2 of 2

